
Physics and Technology of High-k Materials 9

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Table of Contents

<i>Preface</i>	<i>iii</i>
----------------	------------

Chapter 1 **Ge/GeSi Channels**

(Invited) MOS Interface Control Technologies for III-V/Ge Channel MOSFETs <i>S. Takagi, R. Zhang, T. Hoshii, N. Taoka, and M. Takenaka</i>	3
---	---

Interaction of Aluminum Oxide with Germanium during Thermal Annealing in Ar, N ₂ /H ₂ O ₂ , or H ₂ O <i>C. Radtke, N. Molina Bom, G. Vieira Soares, C. Krug, and I. Jacob Rabin Baumvol</i>	21
---	----

Fabrication of High- κ /Ge Stacks with High Quality GeO ₂ Interlayer <i>Y. Suzuki, Y. Oniki, Y. Iwazaki, and T. Ueno</i>	29
---	----

Theoretical Study of Ge Dangling Bonds in GeO ₂ and Correlation with ESR Results at Ge/GeO ₂ Interfaces <i>M. Houssa, G. Pourtois, E. Scalise, V. Afanas'ev, and A. Stesmans</i>	39
--	----

(Invited) Defects and Impurities in Ge-Based Electronic Devices <i>L. Tsetseris</i>	47
--	----

Theoretical and Experimental Demonstration of Electronic State of GeO ₂ <i>H. Chang, S. Lu, W. Chang, T. Chou, H. Lan, C. Lin, and C. Liu</i>	53
---	----

Chapter 2 **New Transistor Concepts**

(Invited) Growth of InAs/InAlAs Core-Shell Nanowires on Si and Transistor Application <i>K. Tomioka, T. Tanaka, and T. Fukui</i>	61
--	----

Atomic-Scale Mechanisms of Growth and Doping of Graphene Nano-Ribbons <i>L. Tsetseris and S. Pantelides</i>	71
--	----

(Invited) Gate Stack Technologies for SiC Power MOSFETs	77
---	----

H. Watanabe, T. Hosoi, T. Kirino, Y. Uenishi, A. Chanthaphan, D. Ikeguchi, A. Yoshigoe, Y. Teraoka, S. Mitani, Y. Nakano, T. Nakamura, and T. Shimura

Chapter 3 New Memory and Gate Dielectrics

Light Effects on Charge Trapping and Detrapping of nc-ZnO Embedded ZrHfO High- <i>k</i> MOS Nonvolatile Memories	93
--	----

B. Luo, C. Lin, and Y. Kuo

Enhanced Electrical Properties of Carbon Doped Epitaxial Gd ₂ O ₃ Thin Films on Si Substrates	101
---	-----

A. Laha, A. Bin, P. Babu, A. Fissel, and H. Osten

Evaluation of Al ₂ O ₃ Films for MANOS Memory Device with Oxygen Infusion by Gas Cluster Ion Beam	109
---	-----

K. Nagata, H. Hashiguchi, T. Yamagichi, A. Ogura, H. Oji, J. Son, I. Hirosawa, Y. Tanaka, Y. Hirota, J. Gumpfer, and K. Yamashita

Effects of Iridium Oxide Thickness and Post Annealing Temperature on the Size and Density of Core-Shell IrO _x -Based Nanocrystals of a Nonvolatile Memory Device	115
---	-----

W. Li and J. Yang

Size-Dependent Trapping Effect in Nano-Dot Non-Volatile Memory	121
--	-----

C. Tsai, C. Cheng, T. Chang, K. Chou, A. Chin, and F. Yeh

Chapter 4 Dielectric Deposition and Processing

(Invited) Epitaxial HfO ₂ Thin Films on Si Substrates: Strategy for Sub-1 nm EOT Technology	135
--	-----

S. Migita and H. Ota

The NH ₃ Nitridation Effects on a Al ₂ O ₃ Passivation by Atomic Layer Deposition (ALD) in the HfO ₂ /GaAs Systems	145
--	-----

Y. Cho, D. Suh, D. Ko, Y. Lee, and M. Cho

(Invited) Aluminium Oxide Atomic Layer Deposition on Semiconductor Substrates	149
---	-----

A. Delabie, S. Sioncke, J. Rip, S. Van Elshocht, G. Pourtois, M. Mueller, B. Beckhoff, and K. Pierloot

Study of the Structural and Thermal Properties of Single Crystalline Epitaxial Rare-Earth-Metal Oxide Layers Grown on Si(111)	161
<i>R. Dargis, D. Williams, R. Smith, E. Arkun, S. Semans, G. Vosters, M. Lebby, and A. Clark</i>	
Evaluation of Properties of SiO ₂ Films Fabricated by Plasma Oxidation	169
<i>T. Yamaguchi, K. Nagata, A. Ogura, T. Koganezawa, I. Hirosawa, Y. Kabe, Y. Sato, S. Ishizuka, and Y. Hirota</i>	
Effect of Plasma Treatment on Stress Reduction Induced by Shallow Trench Isolation Filled with Spin-on-Glass Dielectric	177
<i>H. Hashiguchi, K. Nagata, T. Sameshima, Y. Mizukami, A. Ogura, T. Kuroda, Y. Sato, S. Ishizuka, and Y. Hirota</i>	
Structural, Optical and Electrical Properties of Thin Films of Lanthanum Aluminum Oxide Synthesized by Spray Pyrolysis	183
<i>A. N. Meza-Rocha, E. Zaleta-Alejandre, R. Balderas, Z. Rivera, M. Perez-Arrieta, and C. Falcony</i>	
Deposition Mechanism and Electrical Property of CeO ₂ Thin Films by MOCVD with H ₂ O Introduction	193
<i>N. Tada, T. Izu, T. Kitaru, H. Shimada, S. Suzuki, K. Ishibashi, and Y. Yamamoto</i>	

Chapter 5 **III-V Channels**

(Invited) Active Trap Determination at the Interface of Ge and In _{0.53} Ga _{0.47} as Substrates with Dielectric Layers	203
<i>A. Molle, S. Baldovino, L. Lamagna, S. Spiga, A. Lamperti, M. Fanciulli, D. Tsoutsou, E. Golias, A. Dimoulas, G. Brammertz, C. Merckling, and M. Caymax</i>	
In Situ Deposited HfO ₂ with Amorphous-Si Passivation as a Potential Gate Stack for High Mobility (In)GaSb-Based P-MOSFETs	223
<i>P. Nagaiah, V. Tokranov, M. Yakimov, S. Madisetti, A. Greene, S. Novak, R. Moore, H. Bakhrus, and S. Oktyabrsky</i>	
Molecular Beam Epitaxial Growth of 6.1 Semiconductors Heterostructures for Advanced p-type Quantum Well Devices	231
<i>C. Merckling, A. Alian, X. Sun, A. Firrinceli, J. Dekoster, M. Caymax, and M. Heyns</i>	
SF ₆ Plasma Treated High κ Dielectrics Engineering on InP Metal-Oxide-Semiconductor Field-Effect-Transistors	243
<i>Y. Wang, H. Zhao, Y. Chen, F. Xue, F. Zhou, and J. Lee</i>	

In _{0.7} Ga _{0.3} as Tunneling Field-Effect-Transistors with LaAlO ₃ and ZrO ₂ High-k Dielectrics <i>F. Xue, H. Zhao, Y. Chen, Y. Wang, F. Zhou, and J. Lee</i>	249
Si ₃ N ₄ as a Useful Dielectric for InGaAs MIS Stacks <i>I. Krylov, A. Gavrilov, S. Cohen, D. Ritter, and M. Eizenberg</i>	255
Effect of Various Surface Treatments on Chemical Bonding State at La ₂ O ₃ /In _{0.53} Ga _{0.47} As and on In _{0.53} Ga _{0.47} As Surface <i>K. Yamashita, A. Komatsu, M. Watanabe, Y. Numajiri, D. Zade, K. Kakushima, H. Iwai, and H. Nohira</i>	265
Chapter 6 Other Dielectric Materials	
(Invited) Properties of Oxide Heterostructures <i>A. Demkov, A. Posadas, H. Seo, and J. Lee</i>	275
(Invited) Effect of Strain and Dimensionality on the Properties of Manganites <i>C. Adamo, R. Misra, S. Denev, A. Sengupta, J. Mundy, J. Lee, D. Muller, V. Gopalan, P. Schiffer, and D. Schlom</i>	283
Characterization of the Solid State Properties of Anodic Oxides on Ta-Nb Alloys as a Function of the Anodizing Conditions <i>F. Di Franco, G. Zampardi, M. Santamaria, F. Di Quarto, and H. Habazaki</i>	293
Comparison of the Optical Properties of Tantalum Pentoxide, Ta ₂ O ₅ , Anodically Grown from E-beam Deposited Tantalum, Ta, with Ta ₂ O ₅ E-beam Deposited from a Ta ₂ O ₅ Source <i>A. Kulpa and N. A. Jaeger</i>	311
Chapter 7 Characterization	
EOT Scaling and Flatband Voltage Shift with Al Addition into TiN <i>G. Nakamura, T. Hasegawa, S. Consiglio, F. Amano, V. Luong, Y. Trickett, C. S. Wajda, R. D. Clark, G. J. Leusink, and K. Maekawa</i>	317
Tunneling Emitter Bipolar Transistor as a Characterization Tool for Dielectrics and their Interfaces <i>E. Yalon, A. Gavrilov, S. Cohen, D. Mistele, V. Mikhelashvili, B. Meyler, J. Salzman, and D. Ritter</i>	325

Chapter 8

Defects, Traps, and Reliability

(Invited) Voltage Ramp Stress Based Stress-And-Sense Test Method For Reliability Characterization of Hf-Base High-k/Metal Gate Stacks For CMOS Technologies <i>E. Cartier, A. Kerber, S. Krishnan, B. Linder, T. Ando, M. M. Frank, K. Choi, and V. Narayanan</i>	337
Electron Irradiation Effects on Atomic Layer Deposited High-k Gate Dielectrics <i>H. García, H. Castán, S. Dueñas, L. Bailón, F. Campabadal, J. Rafí, M. Zabala, O. Beldarrain, H. Ohyama, K. Takakura, and I. Tsunoda</i>	349
Electrical Characteristics and Temperature Response of Al ₂ O ₃ Gate Dielectrics with and without Nitric Acid Compensation <i>C. Lin and J. Hwu</i>	361
(Invited) Dielectric Breakdown in Ultra-Thin Hf Based Gate Stacks: A Resistive Switching Phenomenon <i>R. Rodriguez, J. Martin-Martinez, A. Crespo-Yepes, M. Porti, M. Nafria, and X. Aymerich</i>	373
A Drain Current - Drain Voltage Relation for MOSFETs with High-k Gate Stacks <i>S. Kar</i>	389
Conduction Currents and Paramagnetic Defect Centers in UV-Illuminated Silicon Nitride Films <i>K. Kobayashi and K. Ishikawa</i>	401
Impact of Constant Voltage Stress on High-k Gate Dielectric for RF IC Performance <i>P. Paliwoda and D. Misra</i>	415

Chapter 9

GaN/AlGaN Channels

Characteristics of Liquid-Phase-Deposited SrTiO ₃ Films on GaN and AlGaN/GaN Wafer <i>T. Wu, P. Sze, C. C. Hu, T. Huang, F. Adriyanto, C. Wu, and Y. Wang</i>	423
Electrical Characteristics of GaN and Si Based Metal-Oxide-Semiconductor (MOS) Capacitors <i>T. Z. Hossain, D. Wei, and J. H. Edgar</i>	429

Near Room-Temperature Liquid-Phase Deposition of Barium-Doped TiO ₂ on n-GaN and its Application to AlGaN/GaN MOSHEMTs <i>C. C. Hu, M. Lin, T. Wu, F. Adriyanto, P. Sze, C. Wu, and Y. Wang</i>	439
Impact of ALD Gate Dielectrics (SiO ₂ , HfO ₂ , and SiO ₂ /HAH) on Device Electrical Characteristics and Reliability of AlGaN/GaN MOSHFET Devices <i>B. Lee, C. Kirkpatrick, Y. Choi, X. Yang, Y. Wang, X. Yang, A. Huang, and V. Misra</i>	445
Chapter 10 Resistive Switching	
(Invited) Synchrotron Radiation Nano-Spectroscopy of Dielectrics for LSI and ReRAM <i>M. Oshima, S. Toyoda, K. Horiba, R. Yasuhara, and H. Kumigashira</i>	453
High Speed Switching Characteristics of Pt/Ta ₂ O ₅ /Cu Memristive Switch <i>P. Shrestha, A. Ochiai, K. P. Cheung, J. P. Campbell, H. Baumgart, and G. Harris</i>	461
High Performance Cu-doped SiO ₂ ReRAM by a Novel Chemical Soak Method <i>F. Chin, W. Yang, T. Chao, Y. Chang, L. Lin, S. Liu, and C. Lin</i>	469
Effect of Top Electrode Material on Resistive Switching Characteristics in MnO ₂ Nonvolatile Memory Devices <i>Y. Tsai, T. Chang, C. Lin, L. Chiang, S. Chen, S. Sze, and T. Tseng</i>	475
Resistive Switching Characteristics of Core-Shell Nanoparticles of Metal-Oxide on Flexible Substrate <i>J. Yoo, Q. Hu, Y. Baek, C. Kang, H. Lee, and T. Yoon</i>	483
Author Index	489